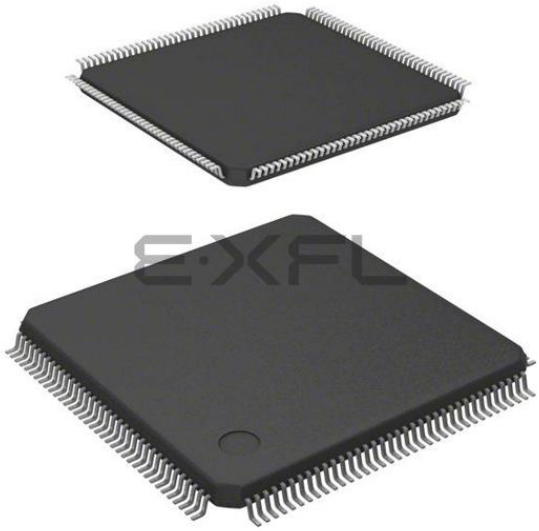

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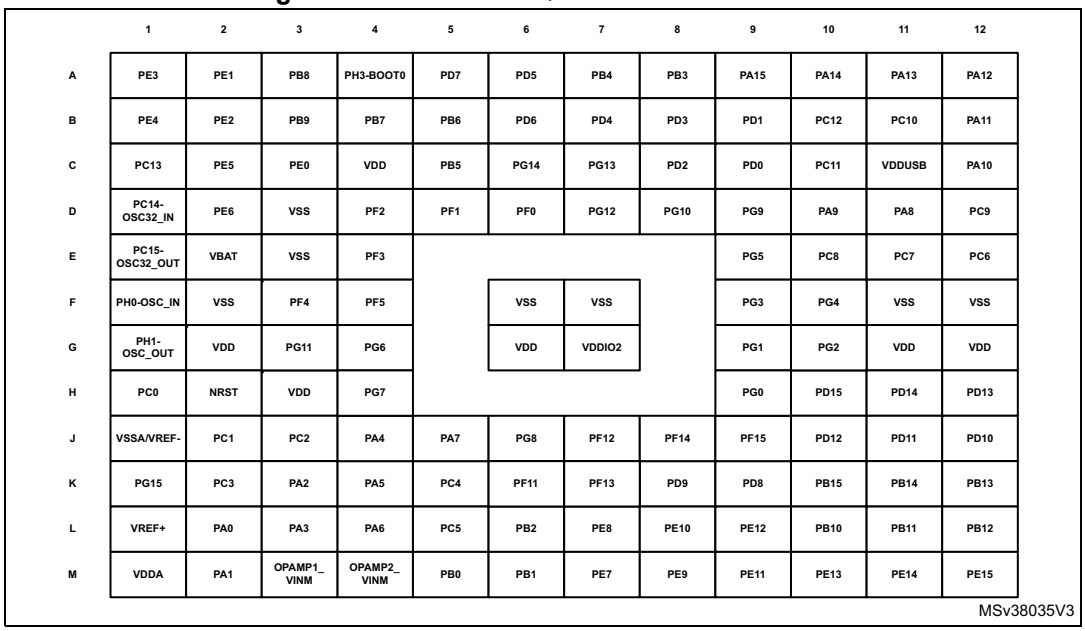
Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, EBI/EMI, I²C, IrDA, LINbus, MMC/SD, QSPI, SAI, SPI, SWPMI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, LCD, PWM, WDT
Number of I/O	115
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	320K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l496zgt6tr

List of figures

Figure 10. STM32L496Qx UFBGA132 ballout(1)



1. The above figure shows the package top view.

Table 14. Legend/abbreviations used in the pinout table

Name		Abbreviation	Definition
Pin name		Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name	
Pin type		S	Supply pin
		I	Input only pin
		I/O	Input / output pin
I/O structure		FT	5 V tolerant I/O
		TT	3.6 V tolerant I/O
		RST	Bidirectional reset pin with embedded weak pull-up resistor
		Option for TT or FT I/Os	
		_f (1)	I/O, Fm+ capable
		_l (2)	I/O, with LCD function supplied by V_{LCD}
		_u (3)	I/O, with USB function supplied by V_{DDUSB}
		_a (4)	I/O, with Analog switch function supplied by V_{DDA}
		_s (5)	I/O supplied only by V_{DDIO2}
Notes		Unless otherwise specified by a note, all I/Os are set as analog inputs during and after reset.	
Pin functions	Alternate functions	Functions selected through GPIOx_AFR registers	
	Additional functions	Functions directly selected/enabled through peripheral registers	

1. The related I/O structures in *Table 15* are: FT_f, FT_fa, FT_fl, FT_fla.
2. The related I/O structures in *Table 15* are: FT_l, FT_fl, FT_lu.
3. The related I/O structures in *Table 15* are: FT_u, FT_lu.
4. The related I/O structures in *Table 15* are: FT_a, FT_la, FT_fa, FT_fla, TT_a, TT_la.
5. The related I/O structures in *Table 15* are: FT_s, FT_fs.

Table 15. STM32L496xx pin definitions (continued)

Pin Number									Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP64	WLCSP100	WLCSP100_SMPS	LQFP100	UFBGA132	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS					Alternate functions	Additional functions
22	K9	K9	31	L4	42	42	M4	M4	PA6	I/O	FT_la	-	TIM1_BKIN, TIM3_CH1, TIM8_BKIN, DCMI_PIXCLK, SPI1_MISO, USART3_CTS, LPUART1_CTS, QUADSPI_BK1_IO3, LCD_SEG3, TIM1_BKIN_COMP2, TIM8_BKIN_COMP2, TIM16_CH1, EVENTOUT	OPAMP2_VINP, ADC12_IN11
-	-	-	-	M4	-	-	N4	N4	OPAMP2_VINM	I	TT	-	-	-
23	J7	G6	32	J5	43	43	L4	L4	PA7	I/O	FT_fla	(1)	TIM1_CH1N, TIM3_CH2, TIM8_CH1N, I2C3_SCL, SPI1_MOSI, QUADSPI_BK1_IO2, LCD_SEG4, TIM17_CH1, EVENTOUT	OPAMP2_VINM, ADC12_IN12
24	H6	K8	33	K5	44	44	H5	H5	PC4	I/O	FT_la	-	USART3_TX, QUADSPI_BK2_IO3, LCD_SEG22, EVENTOUT	COMP1_INM, ADC12_IN13
25	K8	-	34	L5	45	45	J5	J5	PC5	I/O	FT_la	-	USART3_RX, LCD_SEG23, EVENTOUT	COMP1_INP, ADC12_IN14, WKUP5
26	J6	H6	35	M5	46	46	K5	K5	PB0	I/O	TT_la	-	TIM1_CH2N, TIM3_CH3, TIM8_CH2N, SPI1_NSS, USART3_CK, QUADSPI_BK1_IO1, LCD_SEG5, COMP1_OUT, SAI1_EXTCLK, EVENTOUT	OPAMP2_VOUT, ADC12_IN15
27	K7	K7	36	M6	47	47	L5	L5	PB1	I/O	FT_la	-	TIM1_CH3N, TIM3_CH4, TIM8_CH3N, DFSDM1_DATIN0, USART3_RTS_DE, LPUART1_RTS_DE, QUADSPI_BK1_IO0, LCD_SEG6, LPTIM2_IN1, EVENTOUT	COMP1_INM, ADC12_IN16
28	F5	J6	37	L6	48	48	N5	N5	PB2	I/O	FT_la	-	RTC_OUT, LPTIM1_OUT, I2C3_SMBA, DFSDM1_CKIN0, LCD_VLCD, EVENTOUT	COMP1_INP
-	-	-	-	K6	49	49	M5	M5	PF11	I/O	FT	-	DCMI_D12, EVENTOUT	-

Table 15. STM32L496xx pin definitions (continued)

Pin Number									Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP64	WLCSP100	WLCSP100_SMPS	LQFP100	UFBGA132	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS					Alternate functions	Additional functions
-	-	-	60	H12	82	82	K13	K13	PD13	I/O	FT_fl	-	TIM4_CH2, I2C4_SDA, TSC_G6_IO4, LCD_SEG33, FMC_A18, LPTIM2_OUT, EVENTOUT	-
-	-	-	-	-	83	83	H12	H12	VSS	S	-	-	-	-
-	F1	F1	-	-	84	84	H13	H13	VDD	S	-	-	-	-
-	G3	F3	61	H11	85	85	K10	K10	PD14	I/O	FT_l	-	TIM4_CH3, LCD_SEG34, FMC_D0, EVENTOUT	-
-	F4	F2	62	H10	86	86	H11	H11	PD15	I/O	FT_l	-	TIM4_CH4, LCD_SEG35, FMC_D1, EVENTOUT	-
-	-	-	-	G10	87	87	J12	J12	PG2	I/O	FT_s	-	SPI1_SCK, FMC_A12, SAI2_SCK_B, EVENTOUT	-
-	-	-	-	F9	88	88	J11	J11	PG3	I/O	FT_s	-	SPI1_MISO, FMC_A13, SAI2_FS_B, EVENTOUT	-
-	-	-	-	F10	89	89	J10	J10	PG4	I/O	FT_s	-	SPI1_MOSI, FMC_A14, SAI2_MCLK_B, EVENTOUT	-
-	-	-	-	E9	90	90	J9	J9	PG5	I/O	FT_s	-	SPI1_NSS, LPUART1_CTS, FMC_A15, SAI2_SD_B, EVENTOUT	-
-	-	-	-	G4	91	91	G11	G11	PG6	I/O	FT_s	-	I2C3_SMBA, LPUART1_RTS_DE, EVENTOUT	-
-	-	-	-	H4	92	92	H10	H10	PG7	I/O	FT_fs	-	I2C3_SCL, LPUART1_TX, FMC_INT, SAI1_MCLK_A, EVENTOUT	-
-	-	-	-	J6	93	93	H9	H9	PG8	I/O	FT_fs	-	I2C3_SDA, LPUART1_RX, EVENTOUT	-
-	-	-	-	-	94	94	F13	F13	VSS	S	-	-	-	-

Table 15. STM32L496xx pin definitions (continued)

Pin Number									Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP64	WLCSP100	WLCSP100_SMPS	LQFP100	UFBGA132	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS					Alternate functions	Additional functions
-	-	-	-	K1	132	-	C6	-	PG15	I/O	FT_s	-	LPTIM1_OUT, I2C1_SMBA, DCMI_D13, EVENTOUT	COMP2_INM
55	C6	F5	89	A8	133	132	A6	A6	PB3 (JTDO/TRACESWO)	I/O	FT_la	-	JTDO/TRACESWO, TIM2_CH2, SPI1_SCK, SPI3_SCK, USART1_RTS_DE, OTG_FS_CRS_SYNC, LCD_SEG7, SAI1_SCK_B, EVENTOUT	COMP2_INP
56	C7	E6	90	A7	134	133	A5	A5	PB4 (NJTRST)	I/O	FT_fla	-	NJTRST, TIM3_CH1, I2C3_SDA, SPI1_MISO, SPI3_MISO, USART1_CTS, UART5_RTS_DE, TSC_G2_IO1, DCMI_D12, LCD_SEG8, SAI1_MCLK_B, TIM17_BKIN, EVENTOUT	-
57	B7	C7	91	C5	135	134	B5	B5	PB5	I/O	FT_la	-	LPTIM1_IN1, TIM3_CH2, CAN2_RX, I2C1_SMBA, SPI1_MOSI, SPI3_MOSI, USART1_CK, UART5_CTS, TSC_G2_IO2, DCMI_D10, LCD_SEG9, COMP2_OUT, SAI1_SD_B, TIM16_BKIN, EVENTOUT	-
58	A7	A7	92	B5	136	135	C5	C5	PB6	I/O	FT_fa	-	LPTIM1_ETR, TIM4_CH1, TIM8_BKIN2, I2C1_SCL, I2C4_SCL, DFSDM1_DATIN5, USART1_TX, CAN2_TX, TSC_G2_IO3, DCMI_D5, TIM8_BKIN2_COMP2, SAI1_FS_B, TIM16_CH1N, EVENTOUT	COMP2_INP
59	D7	B7	93	B4	137	136	D5	D5	PB7	I/O	FT_fla	-	LPTIM1_IN2, TIM4_CH2, TIM8_BKIN, I2C1_SDA, I2C4_SDA, DFSDM1_CKIN5, USART1_RX, UART4_CTS, TSC_G2_IO4, DCMI_VSYNC, LCD_SEG21, FMC_NL, TIM8_BKIN_COMP1, TIM17_CH1N, EVENTOUT	COMP2_INM, PVD_IN
60	E6	D7	94	A4	138	137	E5	E5	PH3-BOOT0	I/O	FT	-	EVENTOUT	-

Table 16. Alternate function AF0 to AF7 (for AF8 to AF15 see *Table 17*) (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
		SYS_AF	TIM1/2/5/8/ LPTIM1	TIM1/2/3/4/5	SPI2/USART2/ CAN2/TIM8/ QUADSPI	I2C1/2/3/4/ DCMI	SPI1/2/DCMI/ QUADSPI	SPI3/I2C3/ DFSDM/ COMP1/ QUADSPI	USART1/2/3
Port F	PF0	-	-	-	-	I2C2_SDA	-	-	-
	PF1	-	-	-	-	I2C2_SCL	-	-	-
	PF2	-	-	-	-	I2C2_SMBA	-	-	-
	PF3	-	-	-	-	-	-	-	-
	PF4	-	-	-	-	-	-	-	-
	PF5	-	-	-	-	-	-	-	-
	PF6	-	TIM5_ETR	TIM5_CH1	-	-	-	-	-
	PF7	-	-	TIM5_CH2	-	-	-	-	-
	PF8	-	-	TIM5_CH3	-	-	-	-	-
	PF9	-	-	TIM5_CH4	-	-	-	-	-
	PF10	-	-	-	QUADSPI_CLK	-	-	-	-
	PF11	-	-	-	-	-	-	-	-
	PF12	-	-	-	-	-	-	-	-
	PF13	-	-	-	-	I2C4_SMBA	-	DFSDM1_ DATIN6	-
	PF14	-	-	-	-	I2C4_SCL	-	DFSDM1_CKIN6	-
	PF15	-	-	-	-	I2C4_SDA	-	-	-

Table 17. Alternate function AF8 to AF15 (for AF0 to AF7 see *Table 16*) (continued)

Port		AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		UART4/5/ LPUART1/ CAN2	CAN1/TSC	CAN2/ OTG_FS/DCMI/ QUADSPI	LCD	SDMMC/ COMP1/2/FMC/SWPMI1	SAI1/2	TIM2/15/16/17/ LPTIM2	EVENOUT
Port I	PI0	-	-	DCMI_D13	-	-	-	-	EVENTOUT
	PI1	-	-	DCMI_D8	-	-	-	-	EVENTOUT
	PI2	-	-	DCMI_D9	-	-	-	-	EVENTOUT
	PI3	-	-	DCMI_D10	-	-	-	-	EVENTOUT
	PI4	-	-	DCMI_D5	-	-	-	-	EVENTOUT
	PI5	-	-	DCMI_VSYNC	-	-	-	-	EVENTOUT
	PI6	-	-	DCMI_D6	-	-	-	-	EVENTOUT
	PI7	-	-	DCMI_D7	-	-	-	-	EVENTOUT
	PI8	-	-	DCMI_D12	-	-	-	-	EVENTOUT
	PI9	-	CAN1_RX	-	-	-	-	-	EVENTOUT
	PI10	-	-	-	-	-	-	-	EVENTOUT
	PI11	-	-	-	-	-	-	-	EVENTOUT

Table 19. Voltage characteristics(1)

Symbol	Ratings		Min	Max	Unit
V_{DDX} - V_{SS}	External main supply voltage (including V_{DD}, V_{DDA}, V_{DDIO2}, V_{DDUSB}, V_{LCD}, V_{BAT})		-0.3	4.0	V
VDD12 - VSS	External SMPS supply voltage	Range 1	-0.3	1.32	
		Range 2	-0.3		
V_{IN}(2)	Input voltage on FT_xxx pins		V_{SS}-0.3	min (V_{DD}, V_{DDA}, V_{DDIO2}, V_{DDUSB}, V_{LCD}) + 4.0(3)(4)	
	Input voltage on TT_xx pins		V_{SS}-0.3	4.0	
	Input voltage on BOOT0 pin		V_{SS}	9.0	
	Input voltage on any other pins		V_{SS}-0.3	4.0	
$\lvert\Delta V_{DDx}\rvert$	Variations between different V_{DDX} power pins of the same domain		-	50	mV
$\lvert V_{SSx}-V_{SS}\rvert$	Variations between all the different ground pins(5)		-	50	mV

1. All main power (V_{DD}, V_{DDA}, V_{DDIO2}, V_{DDUSB}, V_{LCD}, V_{BAT}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. V_{IN} maximum must always be respected. Refer to *Table 20: Current characteristics* for the maximum allowed injected current values.
3. This formula has to be applied only on the power supplies related to the IO structure described in the pin definition table.
4. To sustain a voltage higher than 4 V the internal pull-up/pull-down resistors must be disabled.
5. Include VREF- pin.

Table 20. Current characteristics

Symbol	Ratings	Max	Unit
ΣIV_{DD}	Total current into sum of all V_{DD} power lines (source)(1) (2)	150	mA
ΣIV_{SS}	Total current out of sum of all V_{SS} ground lines (sink)(1)	150	
$IV_{DD(PIN)}$	Maximum current into each V_{DD} power pin (source)(1)(2)	100	
$IV_{SS(PIN)}$	Maximum current out of each V_{SS} ground pin (sink)(1)	100	
$I_{IO(PIN)}$	Output current sunk by any I/O and control pin except FT_f	20	
	Output current sunk by any FT_f pin	20	
	Output current sourced by any I/O and control pin	20	
$\Sigma I_{IO(PIN)}$	Total output current sunk by sum of all I/Os and control pins(3)	100	
	Total output current sourced by sum of all I/Os and control pins(3)	100	
$I_{INJ(PIN)}$(4)	Injected current on FT_xxx, TT_xx, RST and B pins, except PA4, PA5	-5/+0(5)	
	Injected current on PA4, PA5	-5/0	
$\Sigma\lvert I_{INJ(PIN)}\rvert$	Total injected current (sum of all I/Os and control pins)(6)	25	

1. All main power (V_{DD}, V_{DDA}, V_{DDIO2}, V_{DDUSB}, V_{LCD}, V_{BAT}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supplies, in the permitted range.
2. Valid also for VDD12 on SMPS Package

6.3.4 Embedded voltage reference

The parameters given in *Table 25* are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 22: General operating conditions*.

Table 25. Embedded internal voltage reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{REFINT}	Internal reference voltage	–40 °C < T_A < +130 °C	1.182	1.212	1.232	V
$t_{S\_vrefint}$ (1)	ADC sampling time when reading the internal reference voltage	-	4(2)	-	-	µs
$t_{start\_vrefint}$	Start time of reference voltage buffer when ADC is enable	-	-	8	12(2)	µs
$I_{DD}(V_{REFINTBUF})$	V_{REFINT} buffer consumption from V_{DD} when converted by ADC	-	-	12.5	20(2)	µA
ΔV_{REFINT}	Internal reference voltage spread over the temperature range	V_{DD} = 3 V	-	5	7.5(2)	mV
T_{Coeff}	Average temperature coefficient	–40°C < T_A < +130°C	-	30	50(2)	ppm/°C
A_{Coeff}	Long term stability	1000 hours, T = 25°C	-	300	1000(2)	ppm
$V_{DDCoeff}$	Average voltage coefficient	3.0 V < V_{DD} < 3.6 V	-	250	1200(2)	ppm/V
V_{REFINT_DIV1}	1/4 reference voltage	-	24	25	26	% V_{REFINT}
V_{REFINT_DIV2}	1/2 reference voltage		49	50	51	
V_{REFINT_DIV3}	3/4 reference voltage		74	75	76	

1. The shortest sampling time can be determined in the application by multiple iterations.
2. Guaranteed by design.

Table 41. Current consumption in Sleep and Low-power sleep modes, Flash ON

Symbol	Parameter	Conditions			TYP					MAX(1)					Unit
		-	Voltage scaling	f_{HCLK}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I_{DD_ALL} (Sleep)	Supply current in sleep mode,	$f_{HCLK} = f_{HSE}$ up to 48 MHz included, bypass mode pll ON above 48 MHz all peripherals disable	Range 2	26 MHz	0.79	0.82	0.95	1.17	1.63	0.9	1.0	1.2	1.7	2.7	mA
				16 MHz	0.54	0.57	0.7	0.92	1.38	0.6	0.7	1.0	1.4	2.4	
				8 MHz	0.33	0.37	0.49	0.71	1.17	0.4	0.5	0.7	1.2	2.2	
				4 MHz	0.23	0.26	0.39	0.61	1.06	0.3	0.4	0.6	1.1	2.1	
				2 MHz	0.18	0.21	0.34	0.56	1.01	0.2	0.3	0.5	1.0	1.0	
				1 MHz	0.16	0.19	0.31	0.53	0.99	0.2	0.3	0.5	1.0	1.0	
				100 kHz	0.13	0.17	0.29	0.51	0.96	0.1	0.3	0.5	1.0	1.9	
			Range 1	80 MHz	2.57	2.62	2.76	3.01	3.53	2.8	2.9	3.2	3.8	4.9	
				72 MHz	2.34	2.38	2.53	2.78	3.29	2.6	2.7	3.0	3.5	4.6	
				64 MHz	2.1	2.15	2.29	2.54	3.05	2.3	2.4	2.7	3.3	4.4	
				48 MHz	1.58	1.63	1.78	2.03	2.54	1.8	1.9	2.2	2.7	3.8	
				32 MHz	1.11	1.15	1.3	1.54	2.05	1.2	1.4	1.7	2.2	3.3	
				24 MHz	0.87	0.91	1.06	1.3	1.81	1.0	1.1	1.4	1.9	3.0	
				16 MHz	0.63	0.67	0.82	1.06	1.56	0.7	0.8	1.1	1.6	2.7	
I_{DD_ALL} (LPSleep)	Supply current in low-power sleep mode	$f_{HCLK} = f_{MSI}$ all peripherals disable		2 MHz	103	140	270	506	985	130	247	500	990	2025	µA
				1 MHz	74.2	111	245	476	955	100	215	467	963	1999	
				400 kHz	60	89.8	224	457	937	79	194	444	941	1975	
				100 kHz	53.7	84.1	216	448	928	70	185	434	933	1967	

1. Guaranteed by characterization results, unless otherwise specified.

Table 63. Flash memory characteristics(1) (continued)

Symbol	Parameter	Conditions	Typ	Max	Unit
I_{DD}	Average consumption from V_{DD}	Write mode	3.4	-	mA
		Erase mode	3.4	-	
	Maximum current (peak)	Write mode	7 (for 2 µs)	-	
		Erase mode	7 (for 41 µs)	-	

1. Guaranteed by design.

Table 64. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Min(1)	Unit
N_{END}	Endurance	T_A = –40 to +105 °C	10	kcycles
t_{RET}	Data retention	1 kcycle(2) at T_A = 85 °C	30	Years
		1 kcycle(2) at T_A = 105 °C	15	
		1 kcycle(2) at T_A = 125 °C	7	
		10 kcycles(2) at T_A = 55 °C	30	
		10 kcycles(2) at T_A = 85 °C	15	
		10 kcycles(2) at T_A = 105 °C	10	

1. Guaranteed by characterization results.
2. Cycling performed over the whole temperature range.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin.
- A current injection is applied to each input, output and configurable I/O pin.

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 68. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T_A = +105 °C conforming to JESD78A	II level A(1)

1. Negative injection is limited to -30 mA for PF0, PF1, PG6, PG7, PG8, PG12, PG13, PG14.

6.3.13 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DDIOx} (for standard, 3.3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of the -5 µA/+0 µA range) or other functional failure (for example reset occurrence or oscillator frequency deviation).

The characterization results are given in *Table 69*.

Negative induced leakage current is caused by negative injection and positive induced leakage current is caused by positive injection.

Table 69. I/O current injection susceptibility

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}(1)	Injected current on all pins except PA4, PA5, PB0, PF12, PF13, OPAMP1_V1NM, OPAMP2_V1NM	-5	NA	mA
	Injected current on pins PB0, PF12, PF13	0	NA	
	Injected current on OPAMP1_V1NM, OPAMP2_V1NM	0	0	
	Injected current on PA4, PA5 pins	-5	0	

1. Guaranteed by characterization.

Output voltage levels

Unless otherwise specified, the parameters given in the table below are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 22: General operating conditions*. All I/Os are CMOS- and TTL-compliant (FT OR TT unless otherwise specified).

Table 71. Output voltage characteristics(1)

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL}	Output low level voltage for an I/O pin	CMOS port(2) $\|I_{IO}\|$ = 8 mA $V_{DDIOx} \geq 2.7$ V	-	0.4	V
V_{OH}	Output high level voltage for an I/O pin		V_{DDIOx}-0.4	-	
V_{OL}(3)	Output low level voltage for an I/O pin	TTL port(2) $\|I_{IO}\|$ = 8 mA $V_{DDIOx} \geq 2.7$ V	-	0.4	
V_{OH}(3)	Output high level voltage for an I/O pin		2.4	-	
V_{OL}(3)	Output low level voltage for an I/O pin	$\|I_{IO}\|$ = 20 mA $V_{DDIOx} \geq 2.7$ V	-	1.3	
V_{OH}(3)	Output high level voltage for an I/O pin		V_{DDIOx}-1.3	-	
V_{OL}(3)	Output low level voltage for an I/O pin	$\|I_{IO}\|$ = 4 mA $V_{DDIOx} \geq 1.62$ V	-	0.45	
V_{OH}(3)	Output high level voltage for an I/O pin		V_{DDIOx}-0.45	-	
V_{OL}(3)	Output low level voltage for an I/O pin	$\|I_{IO}\|$ = 2 mA 1.62 V ≥ V_{DDIOx} ≥ 1.08 V	-	$0.35_x V_{DDIOx}$	
V_{OH}(3)	Output high level voltage for an I/O pin		$0.65_x V_{DDIOx}$	-	
V_{OLFM+}(3)	Output low level voltage for an FT I/O pin in FM+ mode (FT I/O with "f" option)	$\|I_{IO}\|$ = 20 mA $V_{DDIOx} \geq 2.7$ V	-	0.4	
		$\|I_{IO}\|$ = 10 mA $V_{DDIOx} \geq 1.62$ V	-	0.4	
		$\|I_{IO}\|$ = 2 mA 1.62 V ≥ V_{DDIOx} ≥ 1.08 V	-	0.4	

1. The I_{IO} current sourced or sunk by the device must always respect the absolute maximum rating specified in *Table 19: Voltage characteristics*, and the sum of the currents sourced or sunk by all the I/Os (I/O ports and control pins) must always respect the absolute maximum ratings ΣI_{IO}.
2. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
3. Guaranteed by design.

Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 29* and *Table 72*, respectively.

Unless otherwise specified, the parameters given are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 22: General operating conditions*.

Table 72. I/O AC characteristics(1)(2) (continued)

Speed	Symbol	Parameter	Conditions	Min	Max	Unit
10	Fmax	Maximum frequency	C=50 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	50	MHz
			C=50 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	25	
			C=50 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	5	
			C=10 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	100(3)	
			C=10 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	37.5	
			C=10 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	5	
	Tr/Tf	Output rise and fall time	C=50 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	5.8	ns
			C=50 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	11	
			C=50 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	28	
			C=10 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	2.5	
			C=10 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	5	
			C=10 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	12	
11	Fmax	Maximum frequency	C=30 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	120(3)	MHz
			C=30 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	50	
			C=30 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	10	
			C=10 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	180(3)	
			C=10 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	75	
			C=10 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	10	
	Tr/Tf	Output rise and fall time	C=30 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	3.3	ns
			C=30 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	6	
			C=30 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	16	
Fm+	Fmax	Maximum frequency	C=50 pF, 1.6 V≤V_{DDIOx}≤3.6 V	-	1	MHz
	Tf	Output fall time(4)		-	5	ns

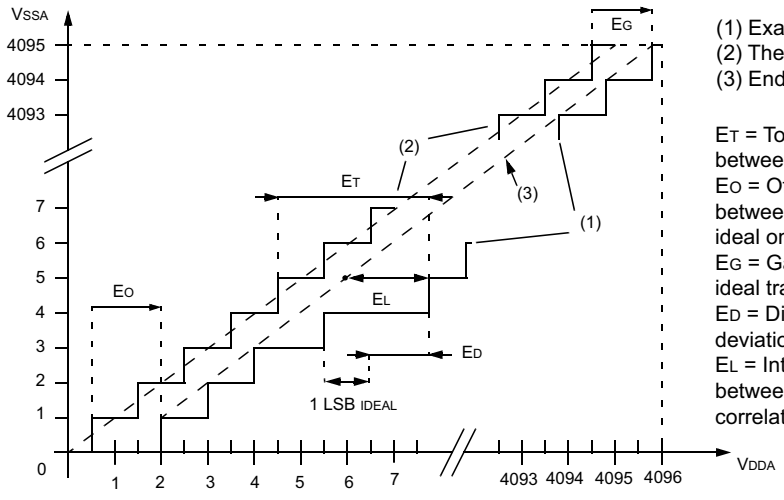
1. The I/O speed is configured using the OSPEEDRy[1:0] bits. The Fm+ mode is configured in the SYSCFG_CFGR1 register. Refer to the RM0351 reference manual for a description of GPIO Port configuration register.
2. Guaranteed by design.
3. This value represents the I/O capability but the maximum system frequency is limited to 80 MHz.
4. The fall time is defined between 70% and 30% of the output waveform accordingly to I^2C specification.

Table 80. ADC accuracy - limited test conditions 4(1)(2)(3) (continued)

Symbol	Parameter	Conditions(4)			Min	Typ	Max	Unit
THD	Total harmonic distortion	ADC clock frequency ≤ 26 MHz, 1.65 V ≤ V_{DDA} = VREF+ ≤ 3.6 V, Voltage scaling Range 2	Single ended	Fast channel (max speed)	-	-71	-69	dB
				Slow channel (max speed)	-	-71	-69	
			Differential	Fast channel (max speed)	-	-73	-72	
				Slow channel (max speed)	-	-73	-72	

1. Guaranteed by design.
2. ADC DC accuracy values are measured after internal calibration.
3. ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
4. The I/O analog switch voltage booster is enable when V_{DDA} < 2.4 V (BOOSTEN = 1 in the SYSCFG_CFGR1 when V_{DDA} < 2.4 V). It is disable when V_{DDA} ≥ 2.4 V. No oversampling.

Figure 31. ADC accuracy characteristics



(1) Example of an actual transfer curve
(2) The ideal transfer curve
(3) End point correlation line

E_T = Total Unajusted Error: maximum deviation between the actual and ideal transfer curves.
E_O = Offset Error: maximum deviation between the first actual transition and the first ideal one.
E_G = Gain Error: deviation between the last ideal transition and the last actual one.
E_D = Differential Linearity Error: maximum deviation between actual steps and the ideal ones.
E_L = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.

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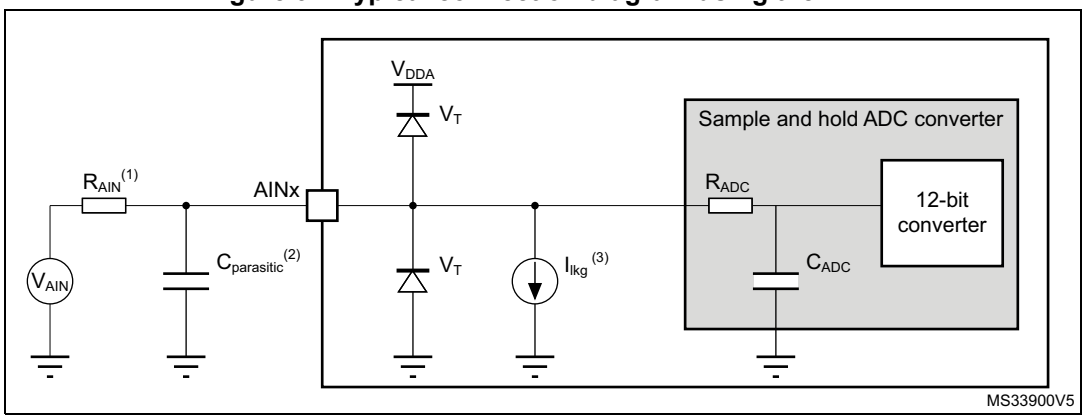
Figure 32. Typical connection diagram using the ADC



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1. Refer to *Table 75: ADC characteristics* for the values of R_{AIN}, R_{ADC} and C_{ADC}.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (refer to *Table 70: I/O static characteristics* for the value of the pad capacitance). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.
3. Refer to *Table 70: I/O static characteristics* for the values of I_{lkg}.

General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 18: Power supply scheme*. The 10 nF capacitor should be ceramic (good quality) and it should be placed as close as possible to the chip.

6.3.27 Communication interfaces characteristics

I²C interface characteristics

The I2C interface meets the timings requirements of the I²C-bus specification and user manual rev. 03 for:

- Standard-mode (Sm): with a bit rate up to 100 kbit/s
- Fast-mode (Fm): with a bit rate up to 400 kbit/s
- Fast-mode Plus (Fm+): with a bit rate up to 1 Mbit/s.

The I2C timings requirements are guaranteed by design when the I2C peripheral is properly configured (refer to RM0351 reference manual).

The SDA and SCL I/O requirements are met with the following restrictions: the SDA and SCL I/O pins are not “true” open-drain. When configured as open-drain, the PMOS connected between the I/O pin and V_{DDIOx} is disabled, but is still present. Only FT_f I/O pins support Fm+ low level output current maximum requirement. Refer to *Section 6.3.14: I/O port characteristics* for the I2C I/Os characteristics.

All I2C SDA and SCL I/Os embed an analog filter. Refer to the table below for the analog filter characteristics:

Table 94. I2C analog filter characteristics(1)

Symbol	Parameter	Min	Max	Unit
t_{AF}	Maximum pulse width of spikes that are suppressed by the analog filter	50(2)	260(3)	ns

1. Guaranteed by design.
2. Spikes with widths below $t_{AF(min)}$ are filtered.
3. Spikes with widths above $t_{AF(max)}$ are not filtered

Table 113. Synchronous non-multiplexed PSRAM write timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FMC_CLK period	$2T_{HCLK}$-0.5	-	ns
$t_{d(CLKL-NExL)}$	FMC_CLK low to FMC_NEx low (x=0..2)	-	2	
$t_{d(CLKH-NExH)}$	FMC_CLK high to FMC_NEx high (x= 0…2)	T_{HCLK}+0.5	-	
$t_{d(CLKL-NADVL)}$	FMC_CLK low to FMC_NADV low	-	0.5	
$t_{d(CLKL-NADVH)}$	FMC_CLK low to FMC_NADV high	0	-	
$t_{d(CLKL-AV)}$	FMC_CLK low to FMC_Ax valid (x=16…25)	-	4	
$t_{d(CLKH-AIV)}$	FMC_CLK high to FMC_Ax invalid (x=16…25)	0	-	
$t_{d(CLKL-NWEL)}$	FMC_CLK low to FMC_NWE low	-	1.5	
$t_{d(CLKH-NWEH)}$	FMC_CLK high to FMC_NWE high	T_{HCLK}+1	-	
$t_{d(CLKL-Data)}$	FMC_D[15:0] valid data after FMC_CLK low	-	3	
$t_{d(CLKL-NBLL)}$	FMC_CLK low to FMC_NBL low	1.5	-	
$t_{d(CLKH-NBLH)}$	FMC_CLK high to FMC_NBL high	T_{HCLK}+0.5	-	
$t_{su(NWAIT-CLKH)}$	FMC_NWAIT valid before FMC_CLK high	2	-	
$t_{h(CLKH-NWAIT)}$	FMC_NWAIT valid after FMC_CLK high	3.5	-	

1. CL = 30 pF.
2. Guaranteed by characterization results.

NAND controller waveforms and timings

Figure 51 through *Figure 54* represent synchronous waveforms, and *Table 114* and *Table 115* provide the corresponding timings. The results shown in these tables are obtained with the following FMC configuration:

- COM.FMC_SetupTime = 0x01
- COM.FMC_WaitSetupTime = 0x03
- COM.FMC_HoldSetupTime = 0x02
- COM.FMC_HiZSetupTime = 0x01
- ATT.FMC_SetupTime = 0x01
- ATT.FMC_WaitSetupTime = 0x03
- ATT.FMC_HoldSetupTime = 0x02
- ATT.FMC_HiZSetupTime = 0x01
- Bank = FMC_Bank_NAND
- MemoryDataWidth = FMC_MemoryDataWidth_16b
- ECC = FMC_ECC_Enable
- ECCPageSize = FMC_ECCPageSize_512Bytes
- TCLRSetupTime = 0
- TARSetupTime = 0

In all timing tables, the T_{HCLK} is the HCLK clock period.

6.3.30 SWPMI characteristics

The Single Wire Protocol Master Interface (SWPMI) and the associated SWPMI_IO transceiver are compliant with the ETSI TS 102 613 technical specification.

Table 117. SWPMI electrical characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{SWPSTART}$	SWPMI regulator startup time	SWP Class B 2.7 V ≤ V_{DD} ≤ 3,3V	-	-	300	µs
t_{SWPBIT}	SWP bit duration	V_{CORE} voltage range 1	500	-	-	ns
		V_{CORE} voltage range 2	620	-	-	

6.3.31 SD/SDIO MMC card host interface (SDIO) characteristics

Unless otherwise specified, the parameters given in *Table 118* for the SDIO/MMC interface are derived from tests performed under the ambient temperature, f_{PCLK2} frequency and V_{DD} supply voltage conditions summarized in *Table 22*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: $0.5V_{DD}$

Refer to *Section 6.3.14: I/O port characteristics* for more details on the input/output characteristics.

Figure 56. SDIO high-speed mode